NSN 5961-01-366-7939

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view Online at https://aerobasegroup.com/nsn/5961-01-366-7939
Inclosure Material:
Metal
Overall Length:
Between 1.172 inches and 1.453 inches
Terminal Length:
0.550 inches
Overall Diameter:
0.667 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-203ab
Mounting Method:
Threaded stud
Features Provided:
Gold plated leads
Overall Width Across Flats:
Between 0.669 inches and 0.688 inches
Thready Qty Per Inch (tpi):
28
Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
50.0 reverse voltage, instantaneous
Current Rating Per Characteristic:
70.00 amperes forward current, dc megahertz
Special Features:
R indicates reverse polarity; junction pattern arrangement: pn
Precious Material And Location:
Terminals gold
Precious Material:
Gold
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:

Specification Data:

81349-mil-s-19500/550 government specification

1 tab, solder lug and 1 threaded stud

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She	lf I	Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0